

# Seydi DoÄan

## List of Publications by Year in descending order

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64  
papers

11,982  
citations

257101

24  
h-index

149479

56  
g-index

65  
all docs

65  
docs citations

65  
times ranked

13557  
citing authors



#	ARTICLE	IF	CITATIONS
19	Effect of n+-GaN subcontact layer on 4H-SiC high-power photoconductive switch. Applied Physics Letters, 2005, 86, 261108.	1.5	27
20	W doped SnO <sub>2</sub> growth via sol-gel routes and characterization: Nanocubes. Optik, 2013, 124, 4827-4831.	1.4	27
21	The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. Applied Physics A: Materials Science and Processing, 2008, 91, 337-340.	1.1	26
22	Capacitance and conductance-frequency characteristics of Au-Sb/p-GaSe:Gd Schottky barrier diode. Vacuum, 2011, 85, 798-801.	1.6	26
23	A study on characterization of Al/ZnS/p-Si/Al heterojunction diode synthesized by sol-gel technique. Materials Letters, 2013, 102-103, 106-108.	1.3	26
24	Growth and Temperature Dependence of Optical Properties of Er Doped and Undoped n-Type InSe. Japanese Journal of Applied Physics, 1999, 38, 5133-5136.	0.8	25
25	GaN/AlGaIn back-illuminated multiple-quantum-well Schottky barrier ultraviolet photodetectors. Solid-State Electronics, 2003, 47, 1401-1408.	0.8	24
26	Forward-current electroluminescence from GaN/ZnO double heterostructure diode. Solid-State Electronics, 2005, 49, 1693-1696.	0.8	24
27	High efficiency n-ZnO/p-SiC heterostructure photodiodes grown by plasma-assisted molecular-beam epitaxy. Superlattices and Microstructures, 2005, 38, 439-445.	1.4	22
28	Surface charging and current collapse in an AlGaIn-GaN heterostructure field effect transistor. Applied Physics Letters, 2005, 86, 083506.	1.5	21
29	Electric field influence on absorption measurement in InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 274-279.	1.3	20
30	Evaluation of Structural and Optical Properties of Mn-Doped ZnO Thin Films Synthesized by Sol-Gel Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2012, 43, 5088-5095.	1.1	19
31	Characteristic evaluation on spray-deposited WFTO thin films as a function of W doping ratio. Rare Metals, 2014, 33, 433-441.	3.6	18
32	Convertibility of conductivity type in reactively sputtered ZnO thin films. Physica Status Solidi A, 2003, 195, 165-170.	1.7	16
33	Thermal stability of electron traps in GaN grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 85, 4058-4060.	1.5	15
34	A study of GaN regrowth on the micro-facetted GaN template formed by in-situ thermal etching. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 718-721.	0.8	15
35	Observation of surface charging at the edge of a Schottky contact. IEEE Electron Device Letters, 2006, 27, 211-213.	2.2	14
36	Comparison of deep levels in GaN grown by MBE, MOCVD, and HVPE. , 2005, , .		13

#	ARTICLE	IF	CITATIONS
37	Electrical characterization of Ag/p-GaSe:Gd schottky barrier diodes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 1958-1962.	1.3	12
38	Urbach tail and electric field influence on optical properties of InSe and InSe:Er single crystals. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 90, 479-485.	1.1	11
39	Structural and optical properties of ZnO thin films by the spin coating Sol-Gel method. <i>Journal of Sol-Gel Science and Technology</i> , 2011, 60, 66-70.	1.1	11
40	Electrical characteristics and inhomogeneous barrier analysis of Au <sup>+</sup> Be/p-InSe: Cd Schottky barrier diodes. <i>Microelectronic Engineering</i> , 2009, 86, 106-110.	1.1	10
41	Temperature dependent capacitance and DLTS studies of Ni/n-type 6H-SiC Schottky diode. <i>Current Applied Physics</i> , 2009, 9, 1181-1185.	1.1	10
42	In situ optical assessment of semi-insulating iron doped InP grown by liquid encapsulated Czochralski process. <i>Journal of Applied Physics</i> , 1999, 85, 6777-6781.	1.1	8
43	Determination of the carrier concentration in InGaAsN <sup>+</sup> GaAs single quantum wells using Raman scattering. <i>Applied Physics Letters</i> , 2004, 85, 4905-4907.	1.5	8
44	Direct recognition of non-radiative recombination centers in semi-insulating LEC InP:Fe using double excitation photoluminescence. <i>Journal of Luminescence</i> , 2008, 128, 232-238.	1.5	8
45	p-GaN-i-GaN/AlGaN multiple-quantum well n-AlGaN back-illuminated ultraviolet detectors. <i>Journal of Electronic Materials</i> , 2003, 32, 307-311.	1.0	7
46	Characterization of MOCVD grown GaN on porous SiC templates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2087-2090.	0.8	7
47	Temperature-dependent electrical characterization of nitrogen-doped ZnO thin film: vacuum annealing effect. <i>Physica Scripta</i> , 2009, 79, 035701.	1.2	7
48	InAlN/GaN heterostructure field-effect transistors on Fe-doped semi-insulating GaN substrates. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 908-911.	0.6	7
49	Development of a photovoltaic panel emulator and LabVIEW <sup>®</sup> -based application platform. <i>Computer Applications in Engineering Education</i> , 2020, 28, 1291-1310.	2.2	7
50	Reduction of threading dislocations in GaN overgrowth by MOCVD on TiN porous network templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005, 202, 749-753.	0.8	5
51	Design of a multi-channel quartz crystal microbalance data acquisition system. <i>Measurement Science and Technology</i> , 2018, 29, 075009.	1.4	5
52	Anomalous Behaviour of Galvanomagnetic Effects in Very Lightly n-Type Bulk GaAs: Possible Role of Reverse-Contrast Centres. <i>Physica Status Solidi A</i> , 1999, 174, 467-475.	1.7	4
53	Temperature Dependence of Magnetoresistance and Hall Effect for Ho Doped n-Type InSe. <i>Physica Scripta</i> , 2000, 62, 92-96.	1.2	4
54	Detection and Imaging of Underground Objects for Distinguishing Explosives by Using a Fluxgate Sensor Array. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 5415.	1.3	4

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55	Determination of the transport mechanisms in mixed conduction of reactively sputtered ZnO thin films. Journal Physics D: Applied Physics, 2008, 41, 135309.	1.3	2
56	Lutentium incorporation influence on ZnO thin films coated via a sol-gel route: spin coating technique. Journal of Materials Science: Materials in Electronics, 2016, 27, 5089-5098.	1.1	2
57	Mobile system: detecting buried objects by magnetic anomaly method. Journal of Applied Remote Sensing, 2021, 15, .	0.6	2
58	Classification of explosives materials detected by magnetic anomaly method. , 2017, , .		1
59	Current conduction mechanisms of heteroepitaxial and homoepitaxial GaN films grown by MBE. , 0, , .		0
60	Deep levels in KOH etched and MOCVD regrown GaN p-n junctions. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2454-2457.	0.8	0
61	Photoionization study of deep centers in GaN/AlGaIn multiple quantum wells. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C3I10-C3I12.	0.6	0
62	Designing a portable data acquisition system for human-computer interface applications. , 2015, , .		0
63	Digital signal processing and classification study for electrooculogram signals. , 2015, , .		0
64	Design of a data acquisition system for passive detection of buried explosives. , 2017, , .		0